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Support Information

Low Temperature UV Cross-linked Fluorinated Polyurethane for Organic Thin Film Transistors

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Table S1 The gel content in DMF for PU and FPUs samples

Sample	M1 (g)	M2 (g)	Gel content (%)
PU	0.0686	0.0649	94.6
FPU-1%	0.1787	0.1675	93.7
FPU-3%	0.1411	0.1298	91.9
FPU-5%	0.1149	0.1070	93.1

M1: Mass before soaking with DMF, M2: Mass after soaking with DMF.

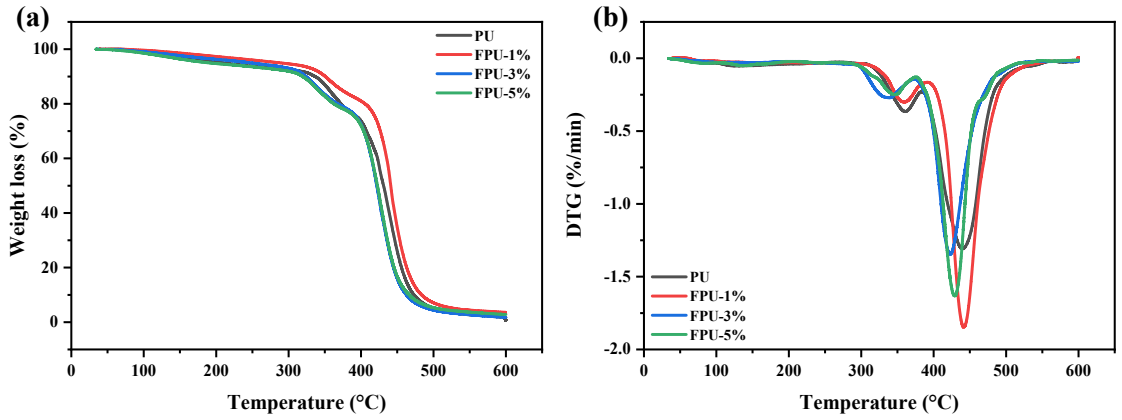

Figure S1 (a) TGA curve and (b) DTG curve for four samples

Table S2 The TGA data of PU and FPUs samples

Sample	T5% (℃)	Tmax1 (℃)	Tmax2 (℃)	Tmax3 (℃)	CR600 (%)
PU	204.6	129.5	360.7	440.5	1.65
FPU-1%	282.4	167.2	359.1	441.6	3.11
FPU-3%	241.7	150.3	334.8	422.4	1.73
FPU-5%	187.5	134.2	342.7	428.2	2.80

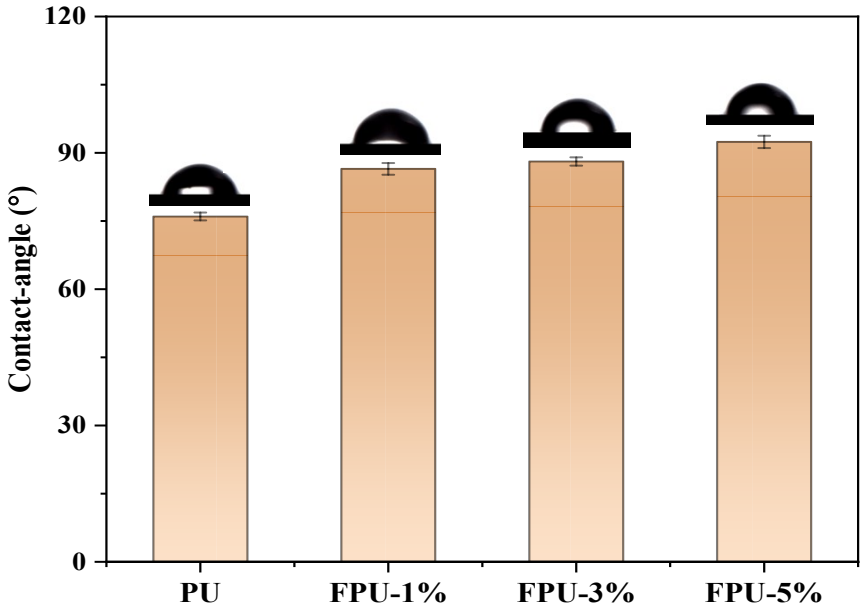

Figure S2 contact angle of four film samples

Table S3 The surface properties of PU and FPUs

Sample	Film thickness (nm)	RMS (nm)	WCA (°)
PU	393.6	0.318	78.5
FPU-1%	413.6	0.351	86.8
FPU-3%	397.1	0.477	88.1
FPU-5%	408.4	0.490	90.1

Table S4 The dielectric properties of PU and FPUs films at 100 Hz

Sample	C_i (nF/cm^2)	κ (100 Hz)	D
PU	8.2	3.9±0.1	1.2
FPU-1%	7.4	3.8±0.2	2.1
FPU-3%	9.9	5.1±0.1	1.3
0.1	12.0	5.8±0.2	5.2